

**N-CHANNEL ENHANCEMENT MODE MOSFET**

### Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
60V	2Ω @ V <sub>GS</sub> = 4.5V	340mA
	2.5Ω @ V <sub>GS</sub> = 2.5V	300mA

### Description

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

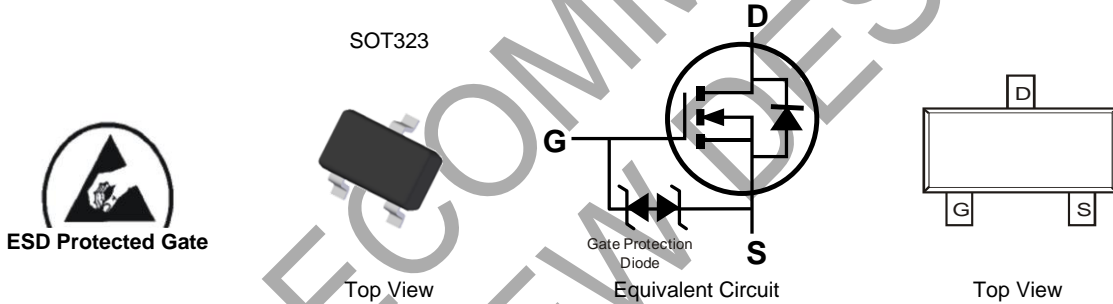
- Motor controls
- Power-management functions
- backlighting

### Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- 100% R<sub>g</sub> Test in Production
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMN62D0UWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**  
<https://www.diodes.com/quality/product-definitions/>

### Mechanical Data

- Package: SOT323
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.006 grams (Approximate)

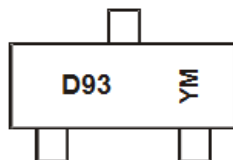


### Ordering Information (Note 4)

Orderable Part Number	Package	Packing	
		Qty.	Carrier
DMN62D0UWQ-7	SOT323	3000	Tape & Reel
DMN62D0UWQ-13	SOT323	10000	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

### Marking Information



D93= Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: L = 2024)  
 M = Month (ex: 9 = September)

#### Date Code Key

Year	2018	-	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	F	-	L	M	N	P	R	S	T	U	V	W

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	60	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 4.5V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	340 270	mA
	t < 5s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	400 300	mA
Maximum Continuous Body Diode Forward Current (Note 6)			I <sub>S</sub>	0.4	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	1.2	A
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)			I <sub>SM</sub>	1.2	A

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Total Power Dissipation (Note 5)			P <sub>D</sub>	320	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		R <sub>θJA</sub>	398	°C/W
	t < 5s			306	
Total Power Dissipation (Note 6)			P <sub>D</sub>	470	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		R <sub>θJA</sub>	273	°C/W
	t < 5s			235	
Operating and Storage Temperature Range			T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 10µA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1.0	µA	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±10	µA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.5	—	1.0	V	V <sub>DS</sub> = 10V, I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>D(S)ON</sub>	—	1.2	2.0	Ω	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 0.1A
		—	1.4	2.5		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 0.05A
		—	1.8	3.0		V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 0.05A
Forward Transconductance	Y <sub>fs</sub>	—	1.8	—	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.2A
Diode Forward Voltage	V <sub>SD</sub>	—	0.8	1.3	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 115mA
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	32	—	pF	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	3.9	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	2.4	—	pF	
Gate Resistance	R <sub>g</sub>	—	101	—	Ω	f = 1MHz, V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V
Total Gate Charge	Q <sub>g</sub>	—	0.5	—	nC	V <sub>GS</sub> = 4.5V, V <sub>DS</sub> = 10V, I <sub>D</sub> = 250mA
Gate-Source Charge	Q <sub>gs</sub>	—	0.09	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	0.09	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	2.4	—	ns	V <sub>DD</sub> = 30V, V <sub>GS</sub> = 10V, R <sub>G</sub> = 25Ω, I <sub>D</sub> = 200mA
Turn-On Rise Time	t <sub>R</sub>	—	2.5	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	22.6	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	12.5	—	ns	

- Notes:
- Device mounted on FR-4 PCB, with minimum recommended pad layout.
  - Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

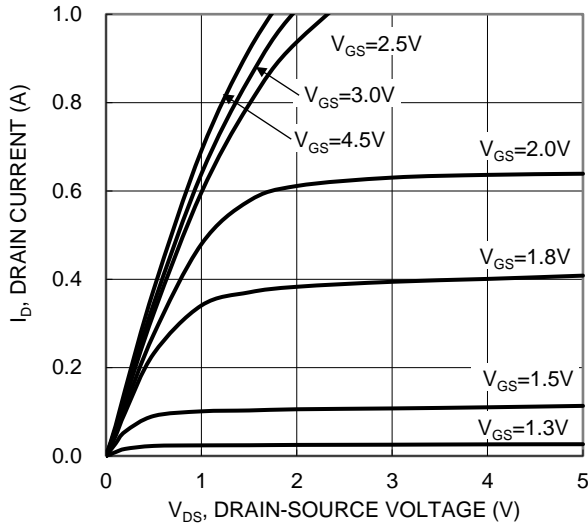


Figure 1. Typical Output Characteristic

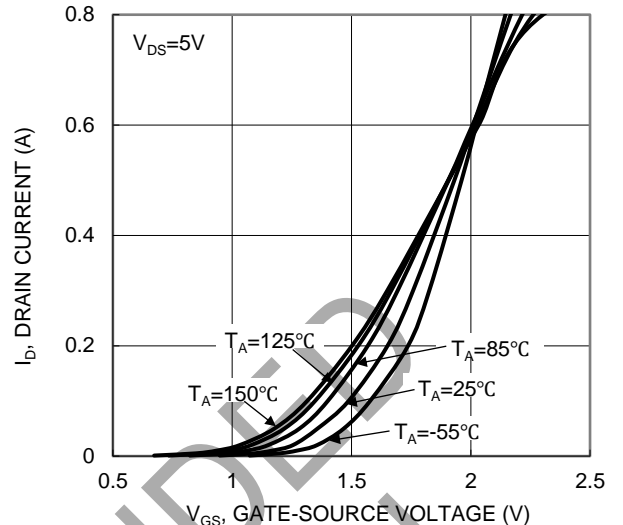


Figure 2. Typical Transfer Characteristic

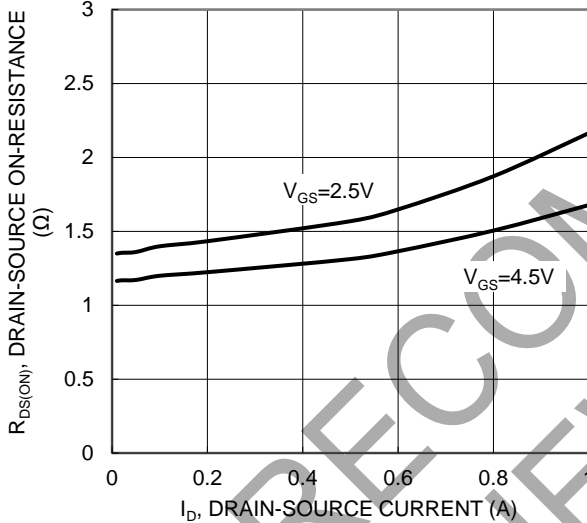


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

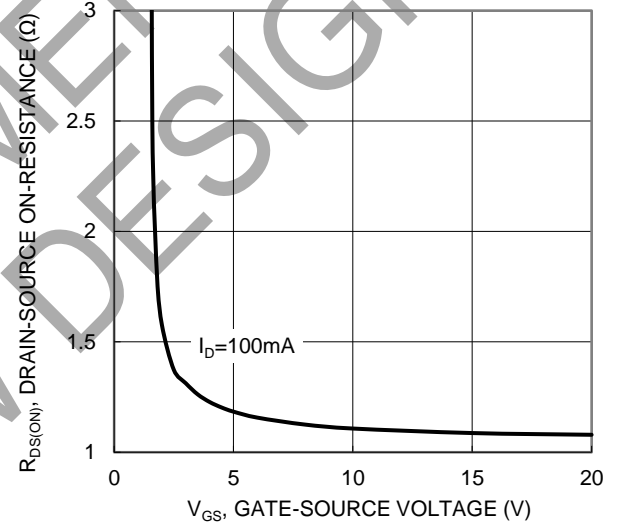


Figure 4. Typical Transfer Characteristic

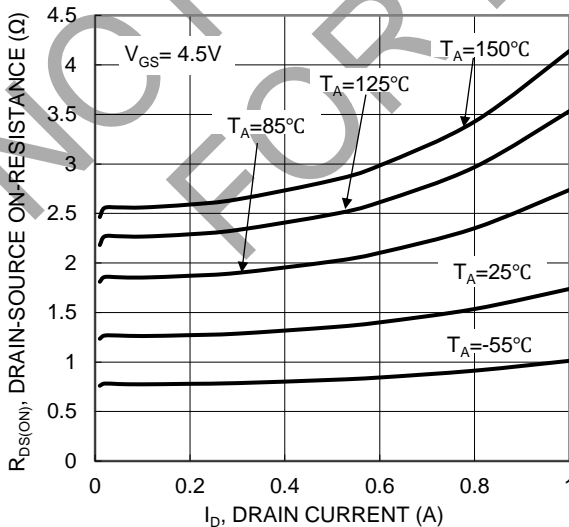


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

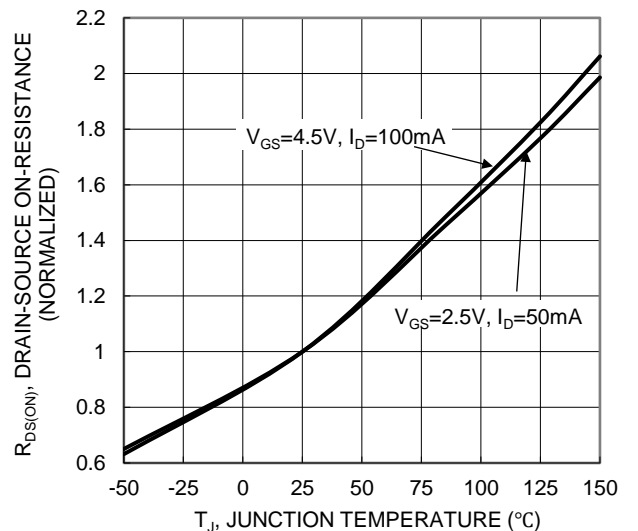


Figure 6. On-Resistance Variation with Junction Temperature

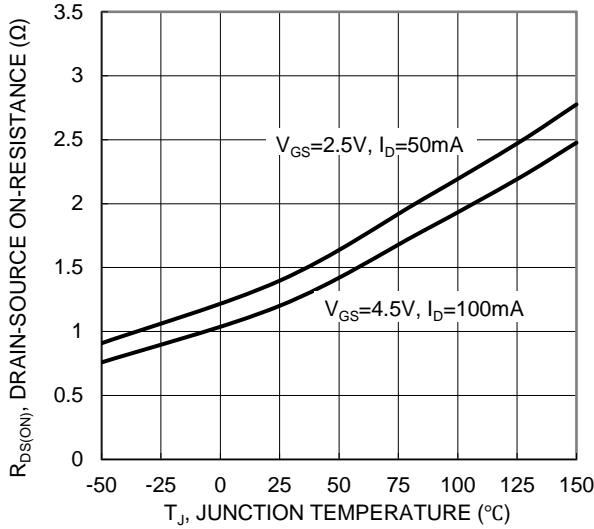


Figure 7. On-Resistance Variation with Junction Temperature

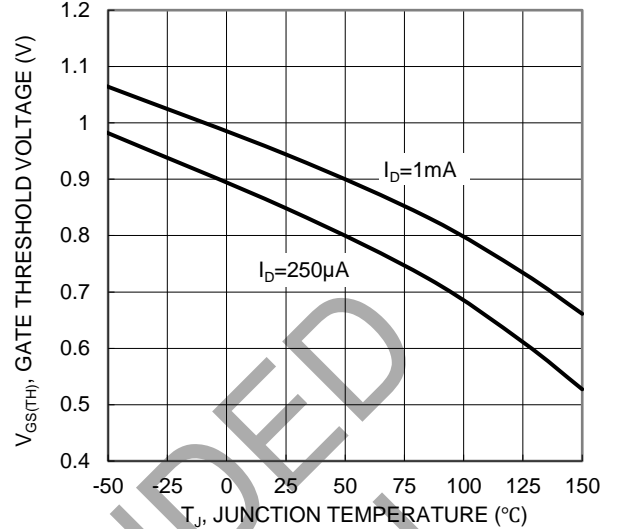


Figure 8. Gate Threshold Variation vs. Junction Temperature

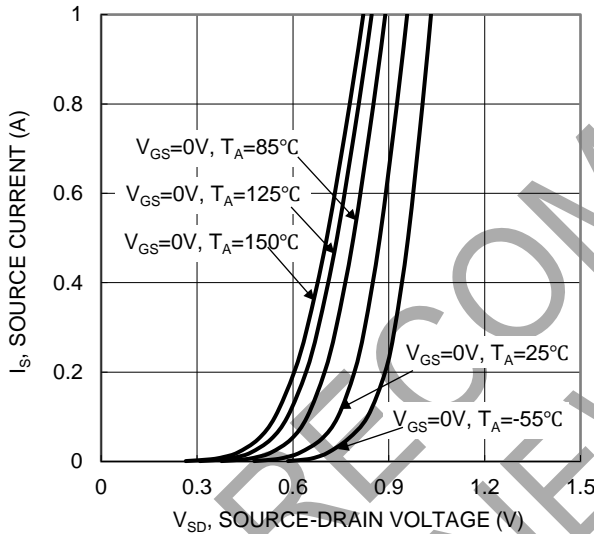


Figure 9. Diode Forward Voltage vs. Current

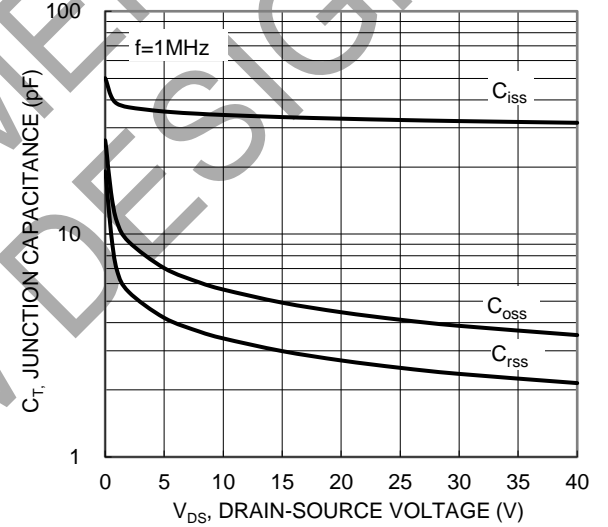


Figure 10. Typical Junction Capacitance

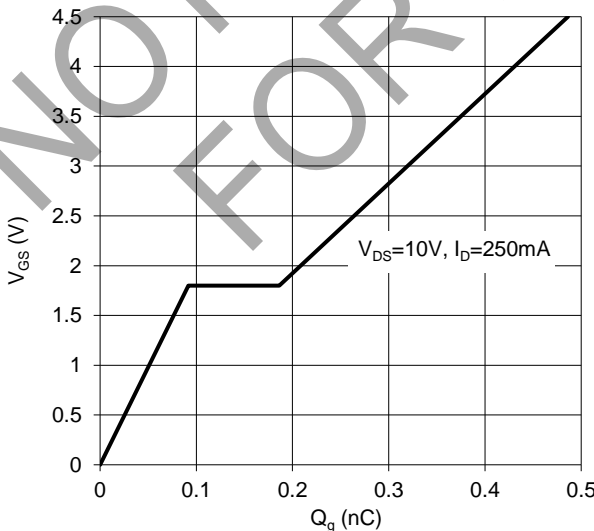


Figure 11. Gate Charge

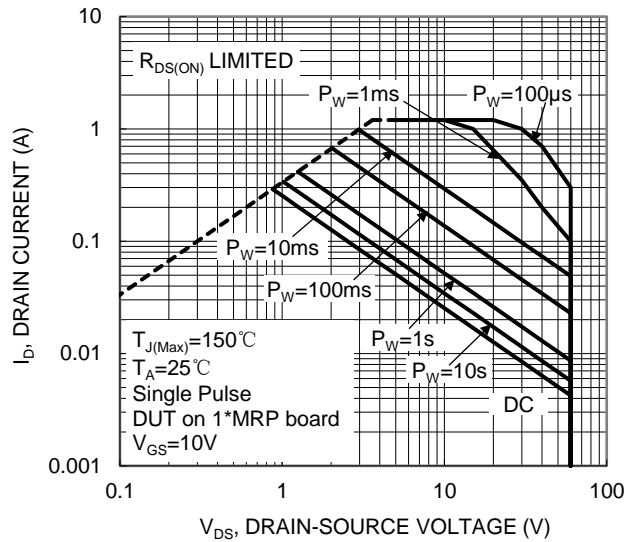


Figure 12. SOA, Safe Operation Area

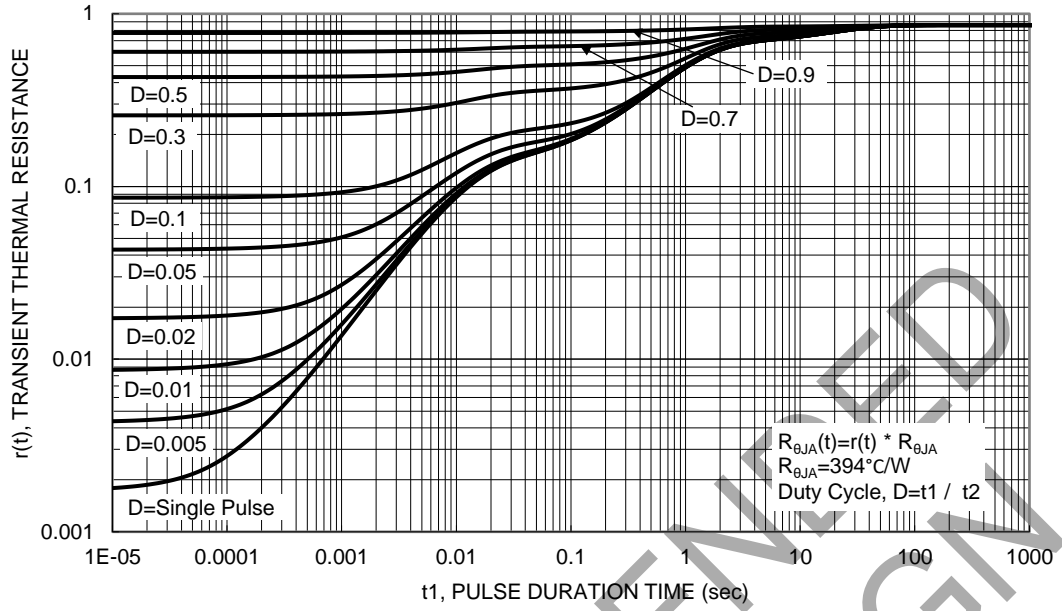


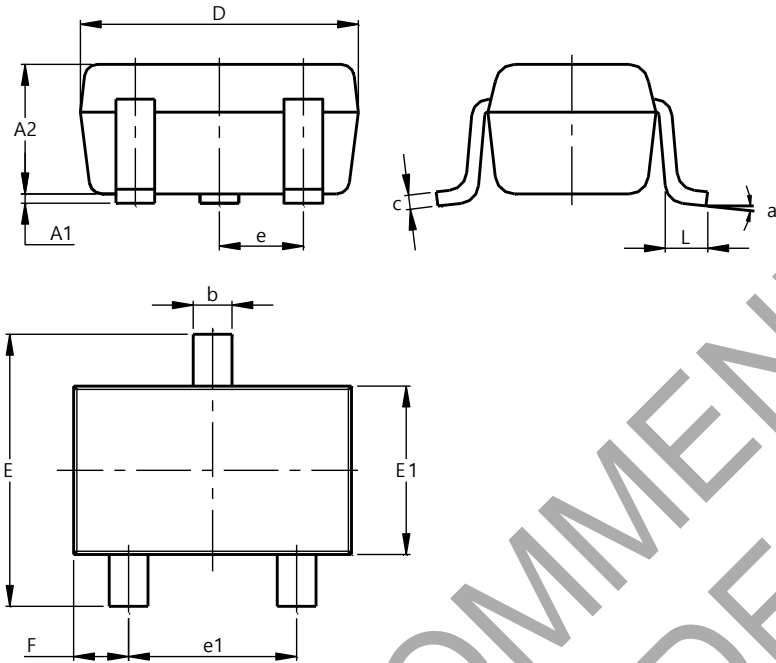
Figure 13. Transient Thermal Resistance

NOT RECOMMENDED FOR NEW DESIGN

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT323**

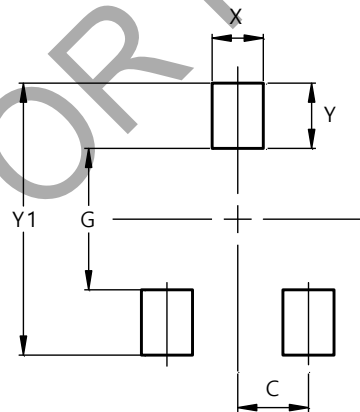


SOT323			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.25	0.40	0.30
c	0.10	0.18	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
e1	1.20	1.40	1.30
F	0.375	0.475	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT323**



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500

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